

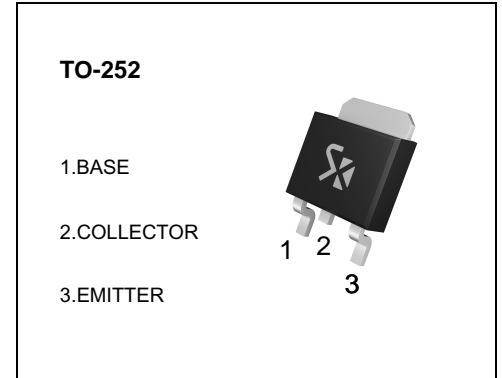
TRANSISTOR (PNP)

FEATURES

- Low speed switching

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

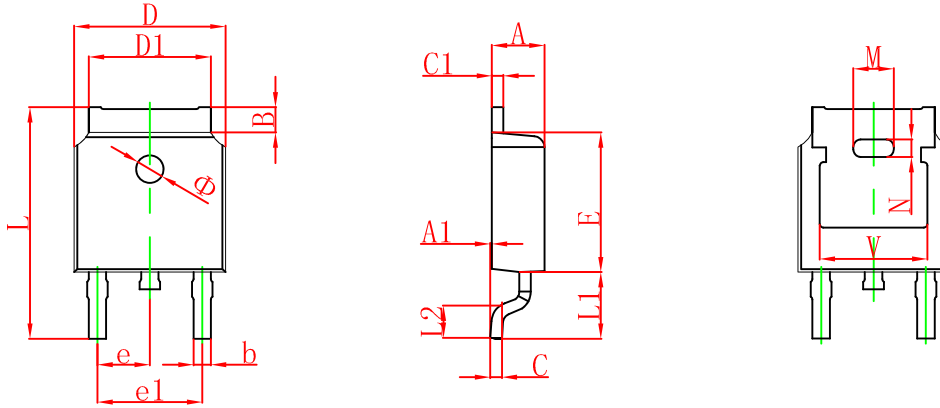
Symbol	Parameter	Value	Unit
V _{CBO}	Collector Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-7	V
I _C	Collector Current –Continuous	-3	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -0.1mA, I _C =0	-7			V
Collector cut-off current	I _{CBO}	V _{CB} = -30V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	100		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -2A, I _B = -200mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -2A, I _B = -200mA			-2	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -0.1A, f=10MHz	50	80		MHz

TO-252 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
φ	1.100	1.300	0.043	0.051

TO-252 Suggested Pad Layout

